

# Outgas from EUV Resist Materials Irradiated with EUV and 2 keV electrons

What is difference?

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# Radiation Effects on Polymers

- Long history and so many papers.
- Reactions : crosslinking, scission (main and side chain scission), and others (double bond formation-coloring, branching etc.).
- Radiation resistant materials for nuclear & fusion reactors.
- Industrial use (crosslinking for cables and graft polymerization for new functional materials)

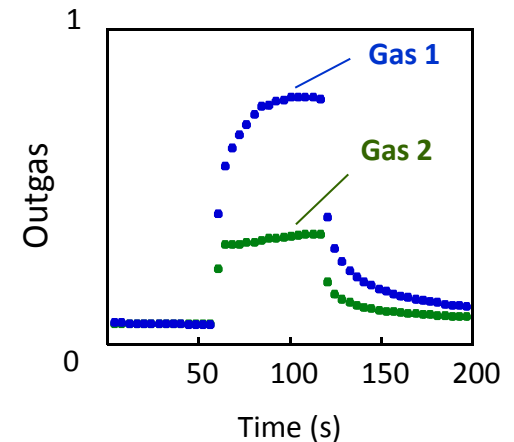
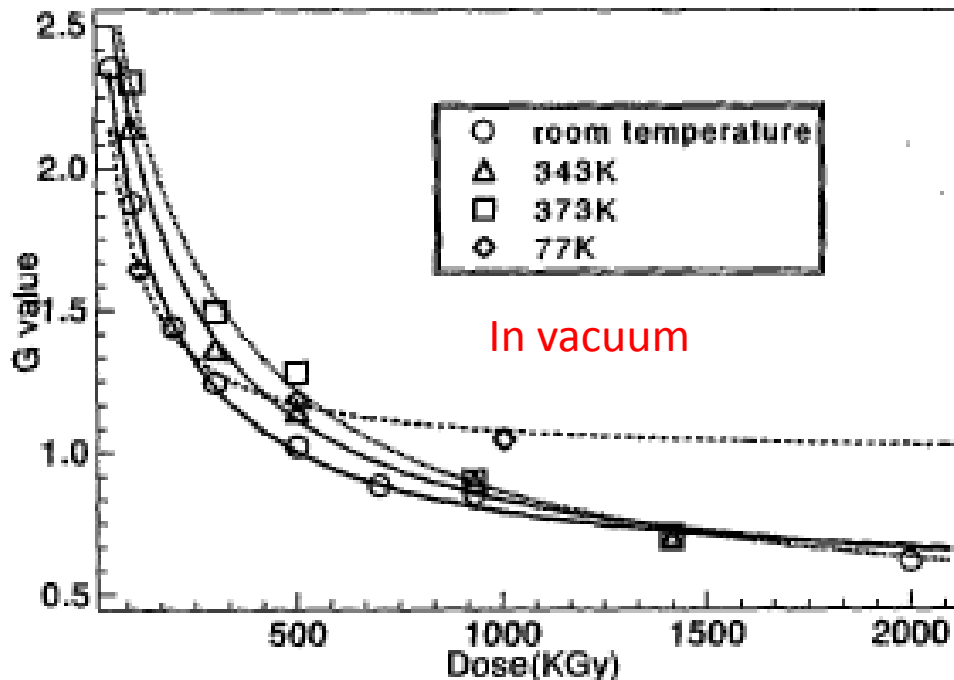
# Typical Example of Radiation Effects on Polymers

## Radiation Effects on Low Density Polyethylene (LDPE)

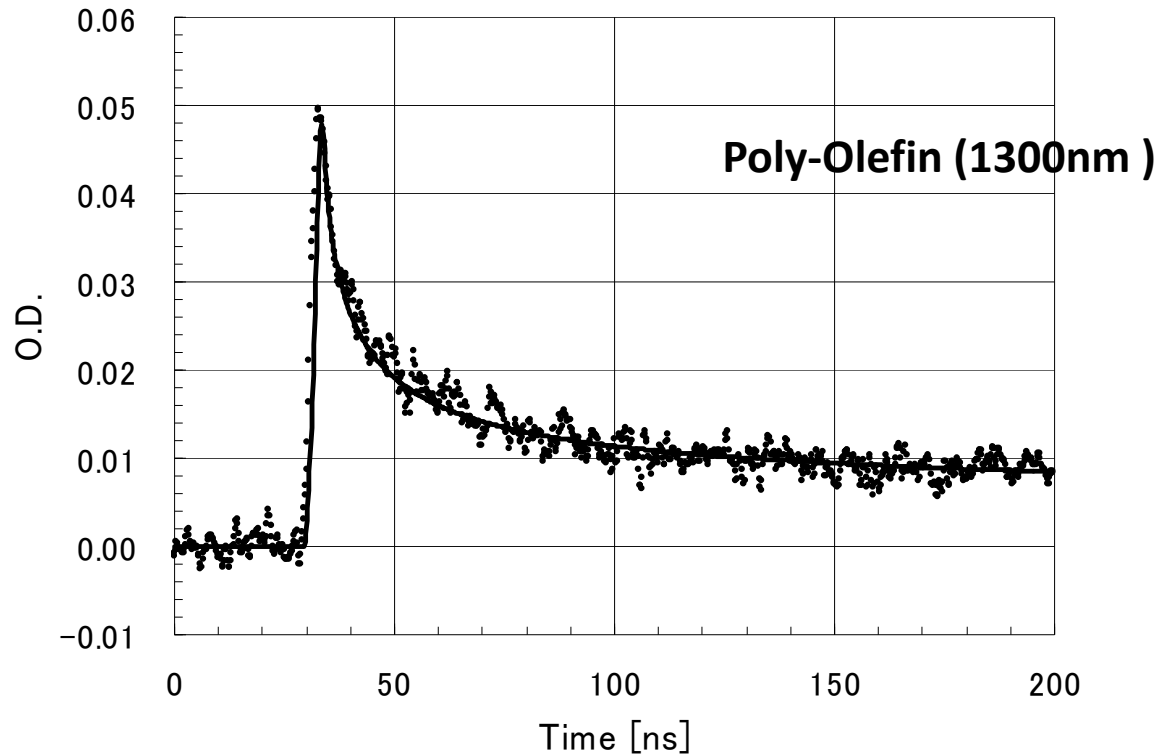
### Dose, Temperature, Atmosphere

Dose:  $\text{mJ}/\text{cm}^2$ ,  $\mu\text{C}/\text{cm}^2$  in lithography

Dose:  $\text{J}/\text{kg}$  (Gy) in radiation chemistry and general science area including nuclear science and technology



Dose dependence of the  $G$ -value for the yield of the trans-vinylene induced in LDPE by  $\gamma$ -ray irradiation at various temperatures.



Ion recombination (geminate recombination ) between electron and positive hole in EB irradiated solid film of polyolefin at 1300 nm (infra-red) at room temperature measured by pulse radiolysis method

# Important Factors in Radiation-Effects on Polymers in Outgas Problem

- Dose Effects
- Dose Rate (Radiation Intensity) Effects
  - Long History for Nuclear Reactor Materials
  - Oxidation is the most and only important problem except for heating.
  - Dose rate can be easily controlled by control of EB current.
- LET (Linear Energy Transfer) Effects
- Stopping (S) Power Effects
- Atmosphere (Temperature Effects, O<sub>2</sub> Effects etc.) Effects

Dose: mJ/cm<sup>2</sup>, μC/cm<sup>2</sup> in lithography

Dose: J/kg (Gy) in radiation chemistry and general science area including nuclear science and technology

# Energy Absorption Process

Charged Particle; Stopping Power (LET) Electron Density

$$\left(-\frac{dE}{dx}\right)_{\text{ion}} = \frac{4\pi e^4}{mc^2} (N_{\text{tar}} Z_{\text{tar}}) \left(\frac{Z_{\text{eff}}^2}{\beta^2}\right) \ln \frac{2mc^2\beta^2}{I}$$

EUV: 92.5 eV light; Lambert Law

Absorption Coefficients of Atoms in Resists

$$\frac{\partial I}{\partial z} = -\alpha I$$

Absorption coefficient ( $\alpha$ )

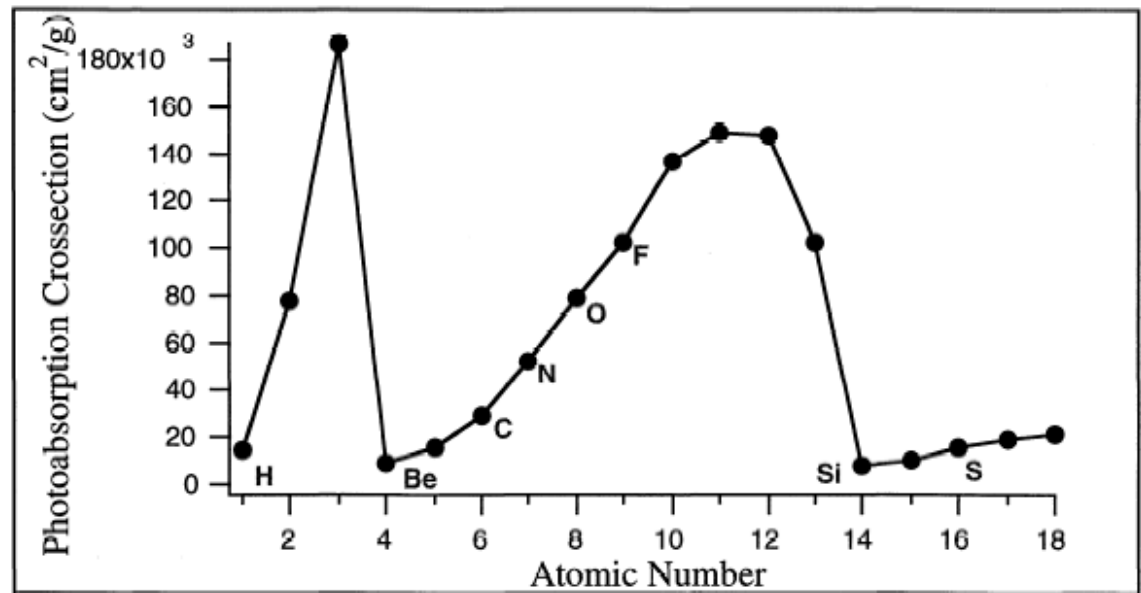


Figure 1: Elemental absorption cross-sections at 13.4 nm wavelength. Elements commonly found in photoresist materials are H, C, N, O, F, and S.

# Interaction of EUV photon with CARs

## -spatial distribution-

Intensity of EUV ( $I$ )

$$\frac{\partial I}{\partial z} = -\alpha I$$

Absorption coefficient ( $\alpha$ )

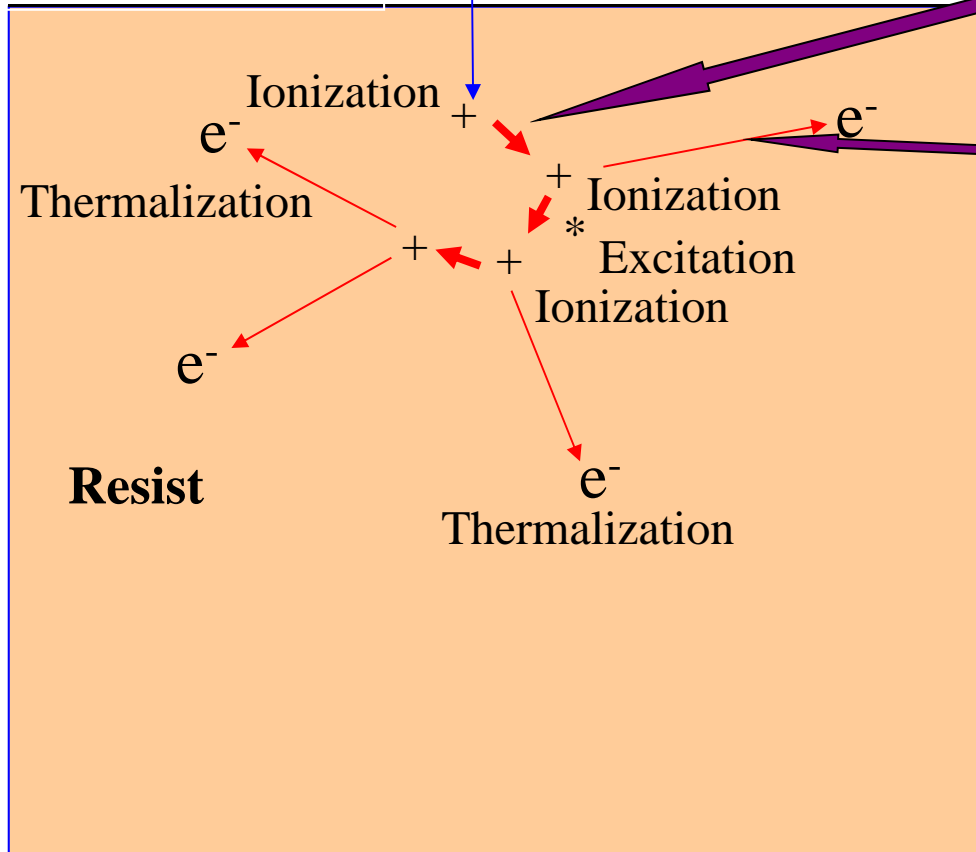
PHS :  $3.8 \mu\text{m}^{-1}$

EUV photon

- ← photon
- ← Electron  $>$  IP
- ← Electron  $<$  IP

Inelastic mean free path

<1 nm mean free path at electron with energy  $>$  IP

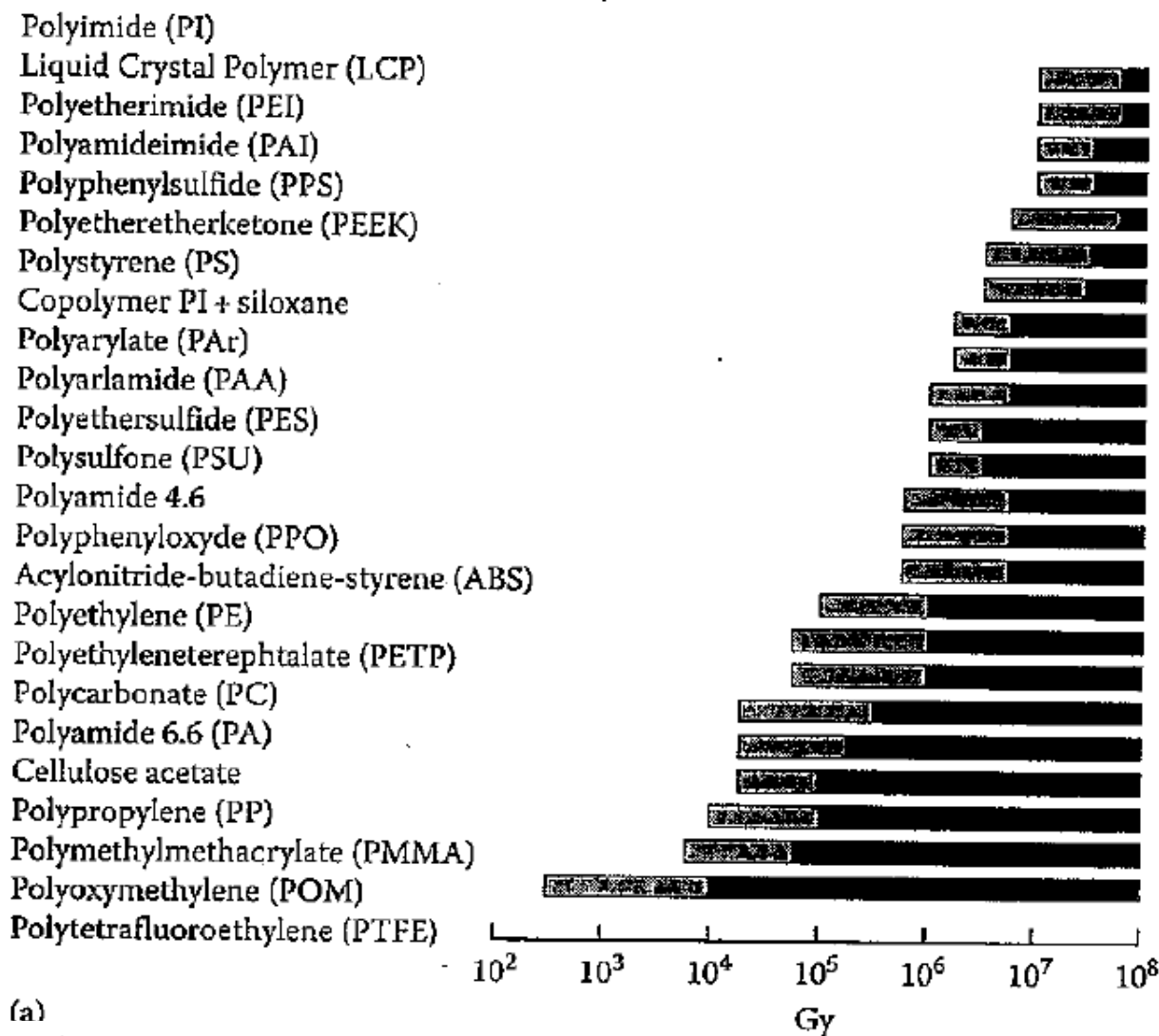


Thermalization Length  
4.0 nm for PHS

↓ The number of secondary electrons is estimated experimentally. 4.2 for PHS

PHS with 10 wt% TPS-tf Acid molecules per photon: 2.6 (Kozawa et al. J.Vac.Sci. Technol.,B25(2007) 2481)

Experimental value: 2.5 (Hirose et al.,Jap.J.Appl.Phys,Part 2(2007))



(a)

General classification of radiation resistance. (a) Rigid thermoplastics.

|  |  |
|--|--|
|  | Mild to moderate damage, utility is often satisfactory |
|  | Moderate to severe damage, use not recommended         |

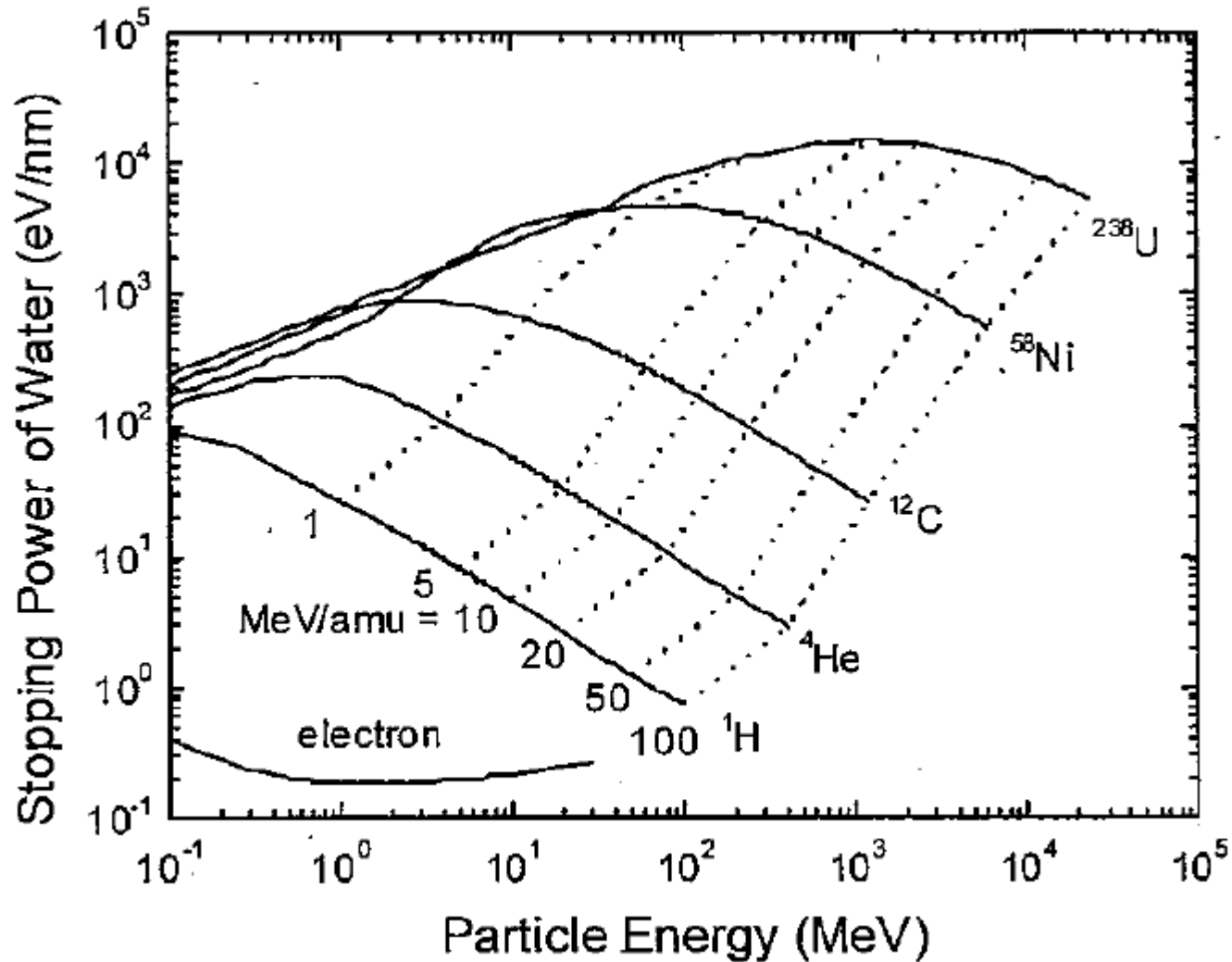
(Reprinted from Tavlet, M. et al., Compilation of radiation damage test data, Part II, 2nd

Dose: mJ/cm<sup>2</sup>, μC/cm<sup>2</sup> in lithography

Dose: J/kg (Gy) in general science aera including nuclear science and technology



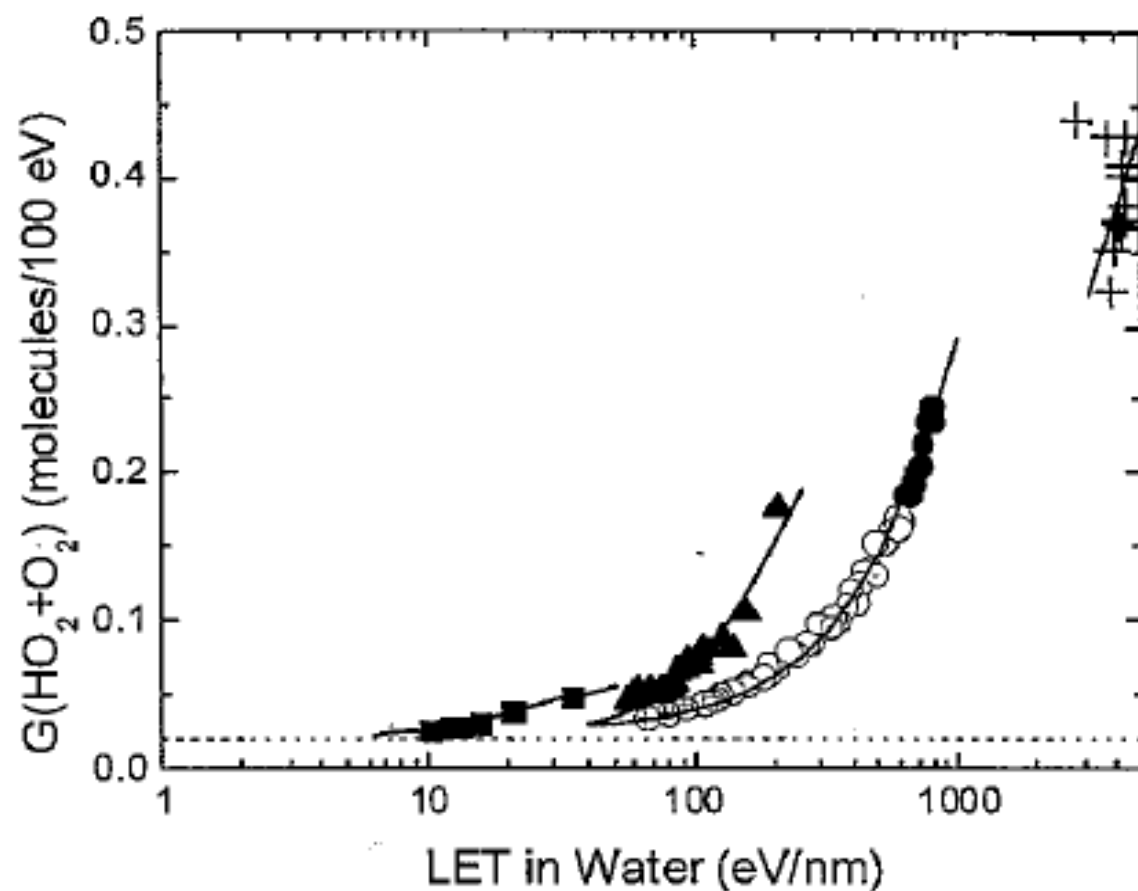
# Stopping Power ( $-dE/dx$ )、LET( $-dE/dx$ )



Stopping power,  $-dE/dx$ , of some heavy ions and electrons in water as a function of energy.

The dotted lines show the stopping power for heavy ions of equal velocity.

Jay. A. LaVerne



**Figure 7** Track average yields of  $\text{HO}_2$  as a function of heavy ion LET: ( $\blacksquare, \blacktriangle, \bullet$ )  $^1\text{H}$ ,  $^4\text{He}$ , and  $^{12}\text{C}$ , Ref. 75; ( $\circ$ )  $^{12}\text{C}$ , Ref. 94; ( $\odot$ )  $^{12}\text{C}$ , Ref. 96; ( $+$ )  $^{58}\text{Ni}$ , Ref. 95. The dotted line is the limiting fast electron yield of 0.02 [123].

# Conclusion

## Important Factors in Radiation-Effects on Polymers in Outgas

- Dose Effects

Dose: mJ/cm<sup>2</sup>, μC/cm<sup>2</sup> in lithography

Dose: J/kg (Gy) in radiation chemistry and general science area including nuclear science and technology

- Dose Rate (Radiation Intensity) Effects

Long History for Nuclear Reactor Materials

(Oxidation is the most and only important problem)

Dose rate can be easily controlled by control of EB current.

- LET (Linear Energy Transfer) Effects

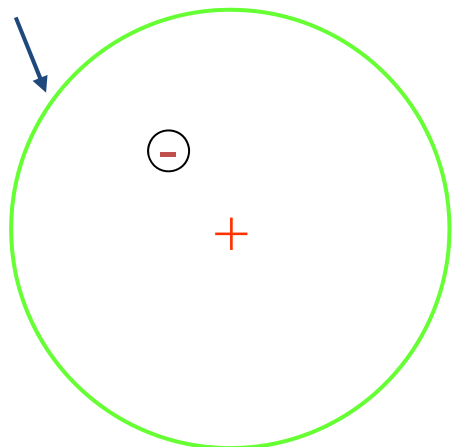
Stopping (S) Power Effects

- Atmosphere (Temperature Effects, O<sub>2</sub> Effects etc.)

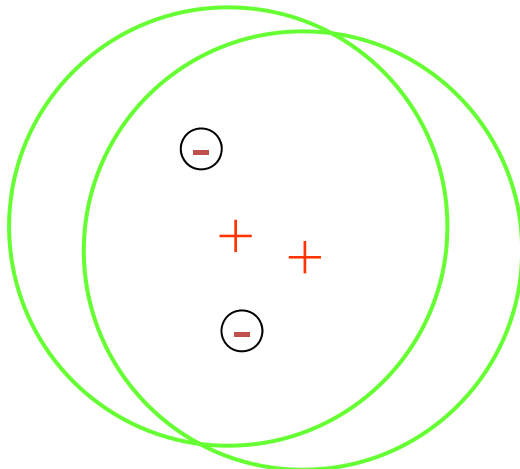
- Generally speaking, difference between EUV and 2 keV exposure in outgas problems is small and controlled, although there is difference.

# Initial configuration of reactive intermediates

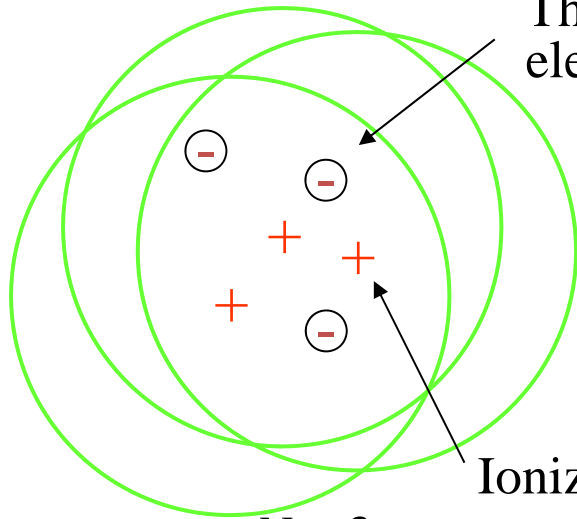
Onsager length ( $\sim 14$  nm in PHS)



$N = 1$



$N = 2$

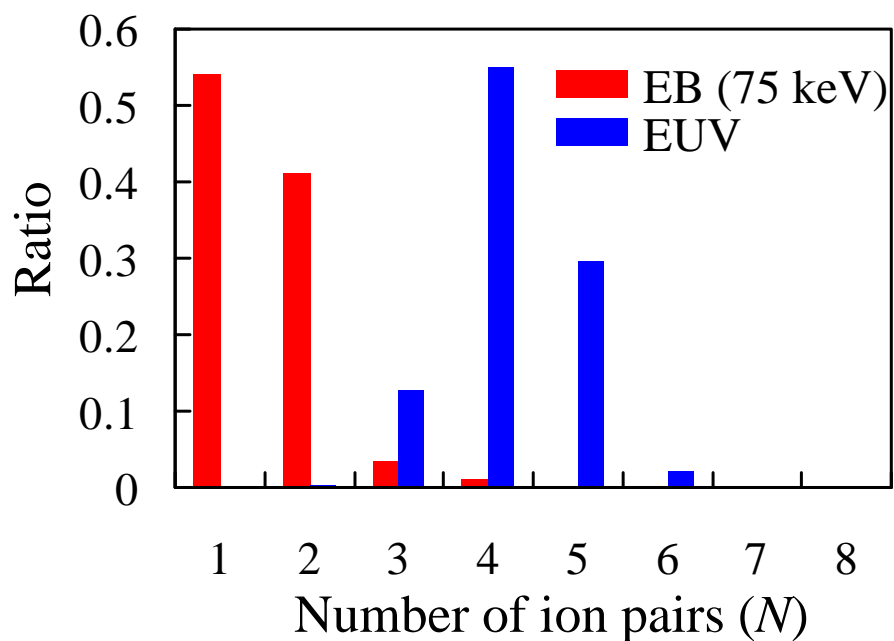


$N = 3$

...

Single spur

Multispur



**Fig.8** Distribution (histogram) of overlapped spurs in EB and EUV resists. The average number is 1.5 for EB and 4.2 for EUV. The energy of incident electrons is 75 keV.

# Difference in sensitization distance between EUV and EB

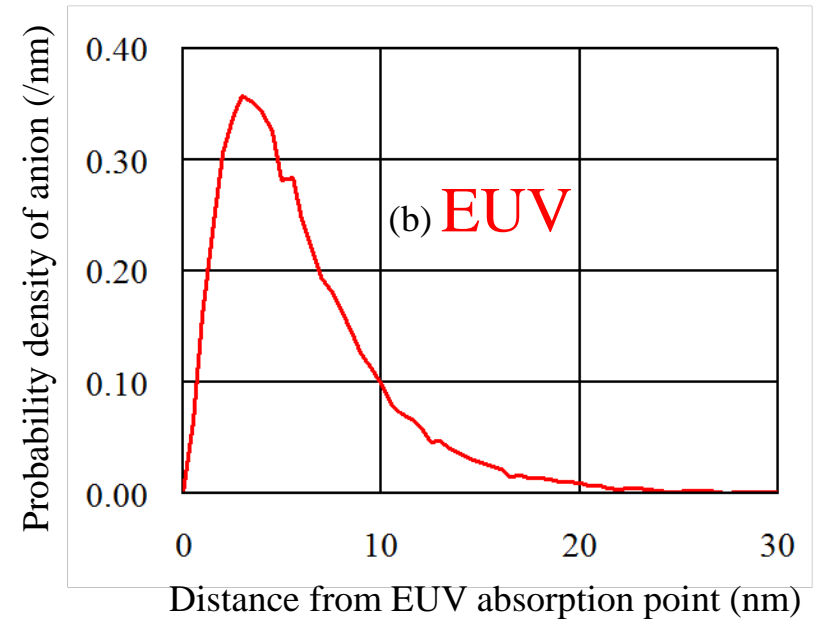
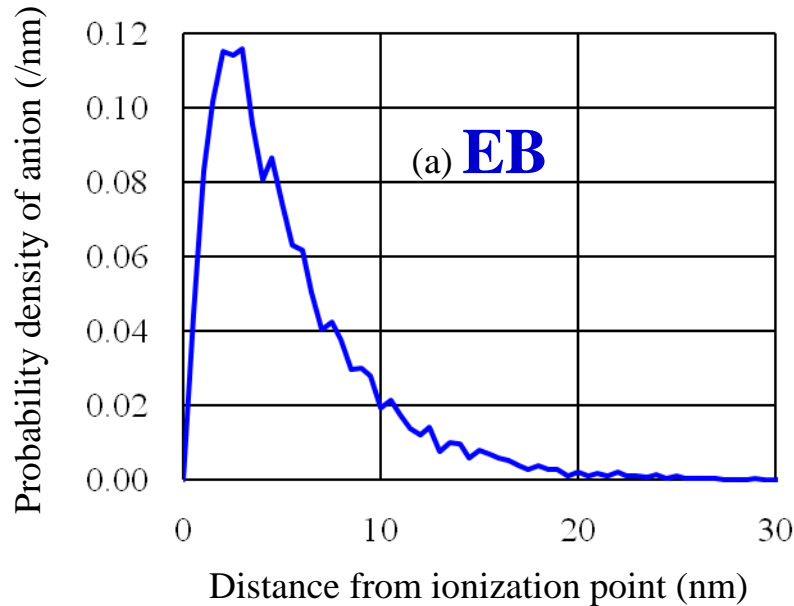


Fig. Probability density of anion generated in PHS with 10 wt% TPS-tf by (a) an electron and (b) an EUV photon.

## Sensitization distance (ionization)

**5.6 nm**

**6.3 nm**

## Acid generation efficiency (ionization)

**0.74 per ionization**

**0.62 per ionization**

$G(\text{acid}) = 3.3$  (3.3 acids per 100 eV)

**2.6 acids per one photon(92.5 eV) in PHS**

Kozawa et al. J.Vac.Sci.Tecnnol.  
B24,3055(2006)

Kozawa and Tagawa, J.Vac.Sci.Tecnnol.,B25(2007) 2481

Experimental value: **2.5** Hirose et al., Jap.J.Appl. Phys, Part 2 Let. & Express Let.,46,L979(2007)

# Acid yield in chemically amplified resist (PHS)

Stopping power in PHS : 57.8 eV/100 nm at 75 keV

G value of ionization in organic materials :  $5 \pm 1$  (per 100 eV absorbed energy)

Acid generation probability : 0.68 (5wt% TPS-tf)

